

MOSFETs Silicon N-channel MOS (U-MOS X-H)

## TK7R0E08QM

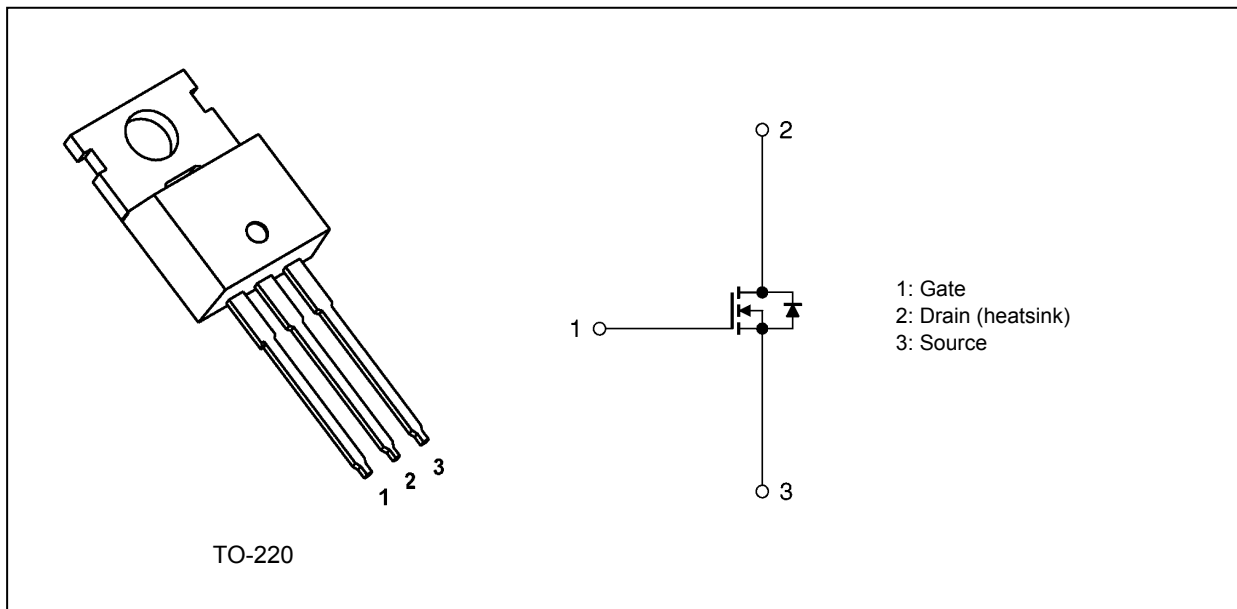
### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 11.6 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{OSS} = 46 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 5.5 \text{ m}\Omega \text{ (typ.) (} V_{GS} = 10 \text{ V)}$
- (5) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A (max) (} V_{DS} = 80 \text{ V)}$
- (6) Enhancement mode:  $V_{th} = 2.5 \text{ to } 3.5 \text{ V (} V_{DS} = 10 \text{ V, } I_D = 0.5 \text{ mA)}$

### 3. Packaging and Internal Circuit



Start of commercial production

2020-11

### 4. Absolute Maximum Ratings (Note) ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Characteristics  | Symbol    | Rating     | Unit             |
|--|-----------|------------|------------------|
| Drain-source voltage   | $V_{DSS}$ | 80         | V                |
| Gate-source voltage  | $V_{GSS}$ | $\pm 20$   |                  |
| Drain current (DC) ( $T_c = 25\text{ }^\circ\text{C}$ ) (Note 1) | $I_D$     | 64         | A                |
| Drain current (DC) (Silicon limit) (Note 1), (Note 2)            | $I_D$     | 82         |                  |
| Drain current (pulsed) ( $t = 100\text{ }\mu\text{s}$ ) (Note 1) | $I_{DP}$  | 240        |                  |
| Power dissipation ( $T_c = 25\text{ }^\circ\text{C}$ )           | $P_D$     | 87         | W                |
| Single-pulse avalanche energy (Note 3)                           | $E_{AS}$  | 38         | mJ               |
| Single-pulse avalanche current (Note 3)                          | $I_{AS}$  | 64         | A                |
| Channel temperature  | $T_{ch}$  | 175        | $^\circ\text{C}$ |
| Storage temperature  | $T_{stg}$ | -55 to 175 |                  |
| Mounting torque  | TOR       | 0.6        | N · m            |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### 5. Thermal Characteristics

| Characteristics  | Symbol         | Max  | Unit                      |
|--|----------------|------|---------------------------|
| Channel-to-case thermal resistance ( $T_c = 25\text{ }^\circ\text{C}$ )    | $R_{th(ch-c)}$ | 1.72 | $^\circ\text{C}/\text{W}$ |
| Channel-to-ambient thermal resistance ( $T_a = 25\text{ }^\circ\text{C}$ ) | $R_{th(ch-a)}$ | 83.3 |                           |

Note 1: Ensure that the channel temperature does not exceed  $175\text{ }^\circ\text{C}$ .

Note 2: Limited 64 A by package capability.

Note 3:  $V_{DD} = 64\text{ V}$ ,  $T_{ch} = 25\text{ }^\circ\text{C}$  (initial),  $L = 7.3\text{ }\mu\text{H}$ ,  $I_{AS} = 64\text{ A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

#### 6.1. Static Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Characteristics                         | Symbol        | Test Condition                                  | Min | Typ. | Max       | Unit             |
|---|---------------|---|-----|------|-----------|------------------|
| Gate leakage current                    | $I_{GSS}$     | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | —   | —    | $\pm 0.1$ | $\mu\text{A}$    |
| Drain cut-off current                   | $I_{DSS}$     | $V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$     | —   | —    | 10        |                  |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$       | 80  | —    | —         | V                |
| Drain-source breakdown voltage (Note 4) | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$     | 60  | —    | —         |                  |
| Gate threshold voltage                  | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 0.5\text{ mA}$     | 2.5 | —    | 3.5       |                  |
| Drain-source on-resistance              | $R_{DS(ON)}$  | $V_{GS} = 6\text{ V}, I_D = 26\text{ A}$        | —   | 7.0  | 9.7       | $\text{m}\Omega$ |
|   |               | $V_{GS} = 10\text{ V}, I_D = 32\text{ A}$       | —   | 5.5  | 7         |                  |

Note 4: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Characteristics                | Symbol    | Test Condition  | Min | Typ. | Max | Unit        |
|--------------------------------|-----------|---|-----|------|-----|-------------|
| Input capacitance              | $C_{iss}$ | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | —   | 2700 | —   | $\text{pF}$ |
| Reverse transfer capacitance   | $C_{rss}$ |   | —   | 45   | —   |             |
| Output capacitance             | $C_{oss}$ |   | —   | 700  | —   |             |
| Gate resistance                | $r_g$     | —   | —   | 1.6  | 2.4 | $\Omega$    |
| Switching time (rise time)     | $t_r$     | See Fig. 6.2.1  | —   | 45   | —   | ns          |
| Switching time (turn-on time)  | $t_{on}$  |   | —   | 60   | —   |             |
| Switching time (fall time)     | $t_f$     |   | —   | 53   | —   |             |
| Switching time (turn-off time) | $t_{off}$ |   | —   | 89   | —   |             |

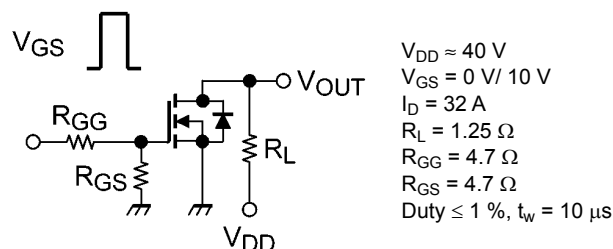


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Characteristics                                 | Symbol    | Test Condition  | Min | Typ. | Max | Unit |
|---|-----------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} \approx 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 32\text{ A}$ | —   | 39   | —   | nC   |
|   |           | $V_{DD} \approx 40\text{ V}, V_{GS} = 6\text{ V}, I_D = 26\text{ A}$  | —   | 24   | —   |      |
| Gate-source charge 1                            | $Q_{gs1}$ | $V_{DD} \approx 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 32\text{ A}$ | —   | 11.5 | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |   | —   | 8.6  | —   |      |
| Gate switch charge                              | $Q_{SW}$  |   | —   | 11.6 | —   |      |
| Output charge                                   | $Q_{oss}$ | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$         | —   | 46   | —   |      |

### 6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Characteristics                         | Symbol  | Test Condition                                   | Min | Typ. | Max  | Unit |
|---|---|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note 5) | $I_{DRP}$<br>( $t = 100\text{ }\mu\text{s}$ ) | —  | —   | —    | 240  | A    |
| Diode forward voltage                   | $V_{DSF}$                                     | $I_{DR} = 32\text{ A}$ , $V_{GS} = 0\text{ V}$   | —   | —    | -1.2 | V    |
| Reverse recovery time                   | $t_{rr}$                                      | $I_{DR} = 16\text{ A}$ , $V_{GS} = 0\text{ V}$ , | —   | 39   | —    | ns   |
| Reverse recovery charge                 | $Q_{rr}$                                      | $-di_{DR}/dt = 100\text{ A}/\mu\text{s}$         | —   | 35   | —    | nC   |

Note 5: Ensure that the channel temperature does not exceed  $175\text{ }^\circ\text{C}$ .

### 7. Marking

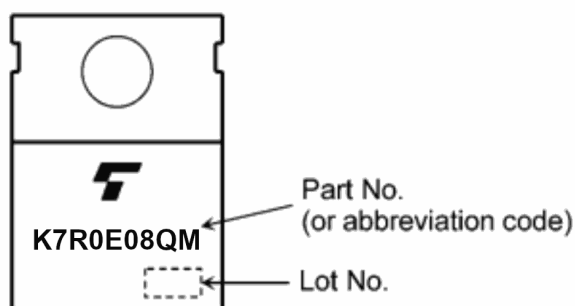
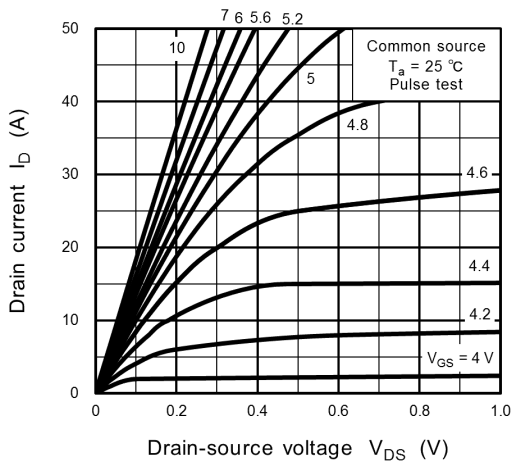
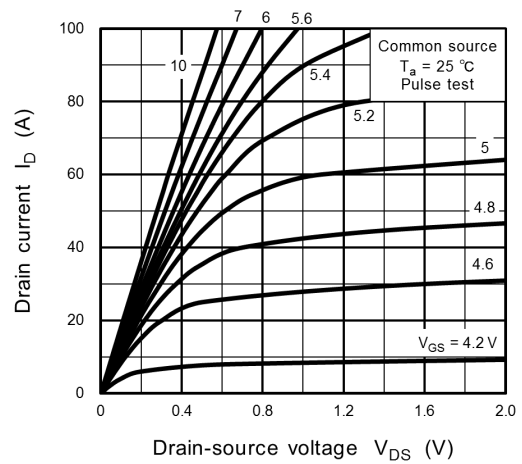


Fig. 7.1 Marking

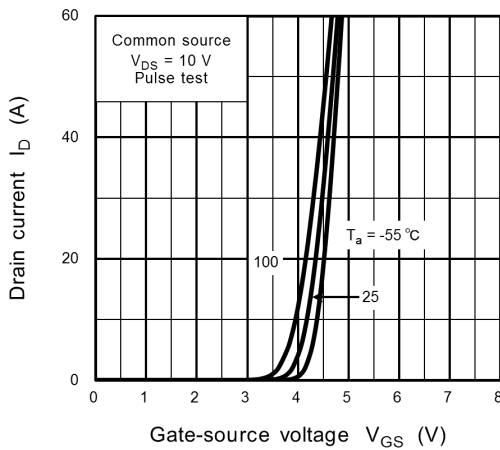
## 8. Characteristics Curves (Note)



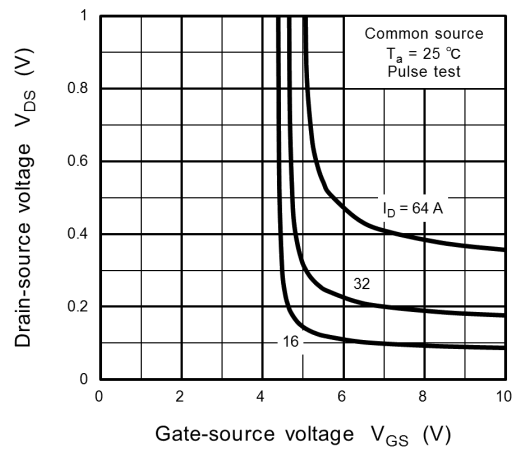
**Fig. 8.1**  $I_D - V_{DS}$



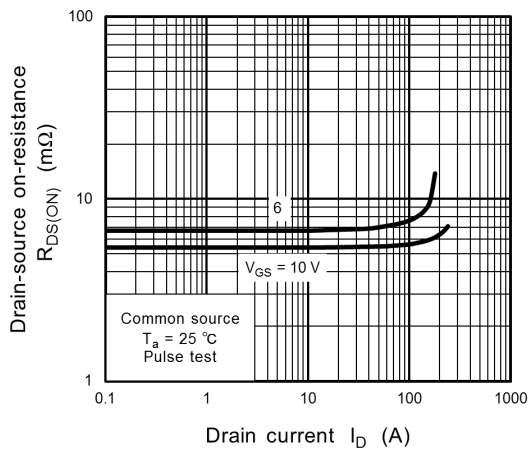
**Fig. 8.2**  $I_D - V_{DS}$



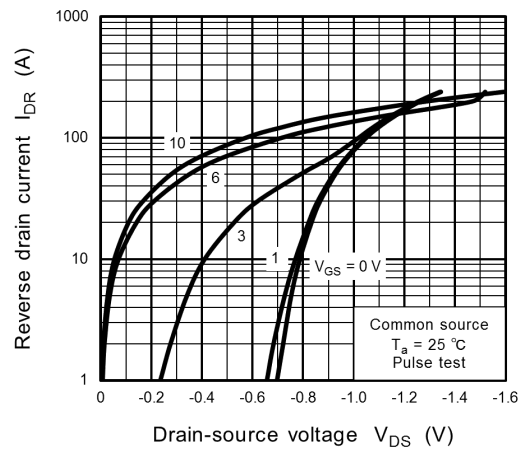
**Fig. 8.3**  $I_D - V_{GS}$



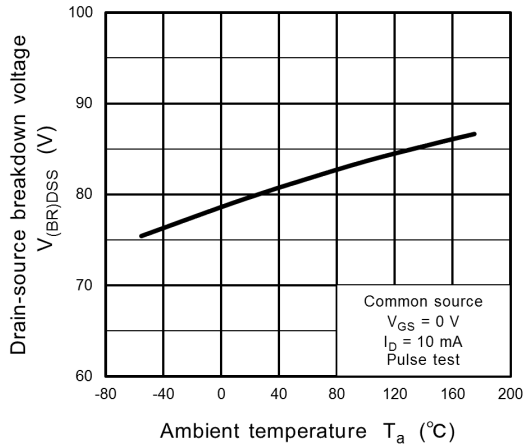
**Fig. 8.4**  $V_{DS} - V_{GS}$



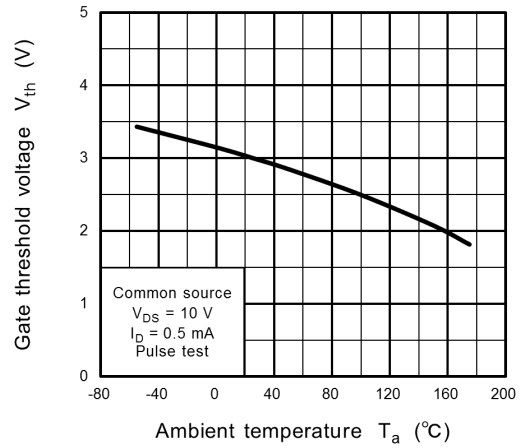
**Fig. 8.5**  $R_{DS(ON)} - I_D$



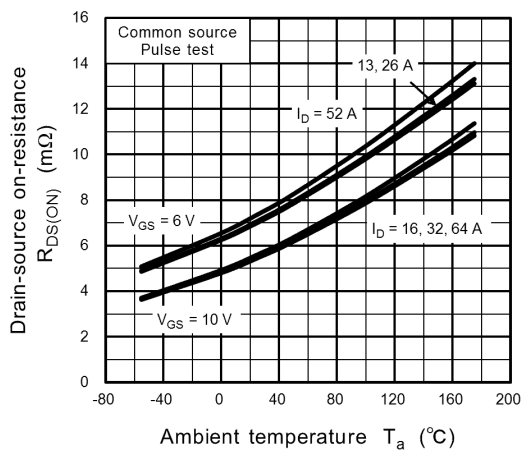
**Fig. 8.6**  $I_{DR} - V_{DS}$



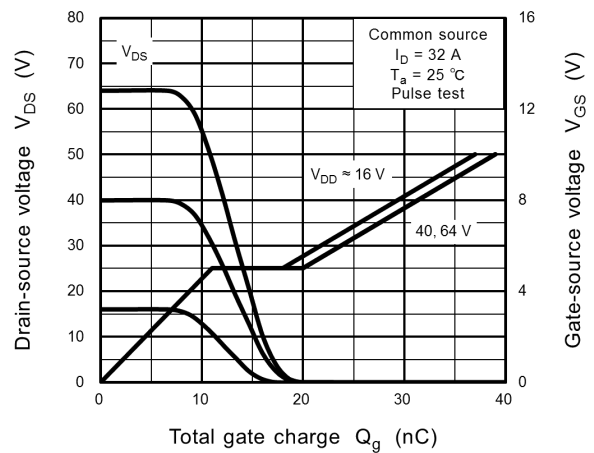
**Fig. 8.7  $V_{(BR)DSS} - T_a$**



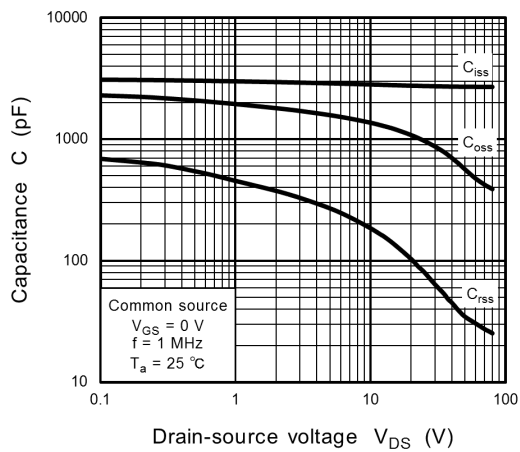
**Fig. 8.8  $V_{th} - T_a$**



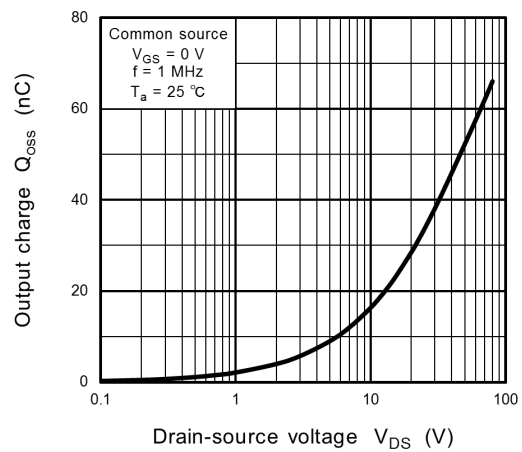
**Fig. 8.9  $R_{DS(ON)} - T_a$**



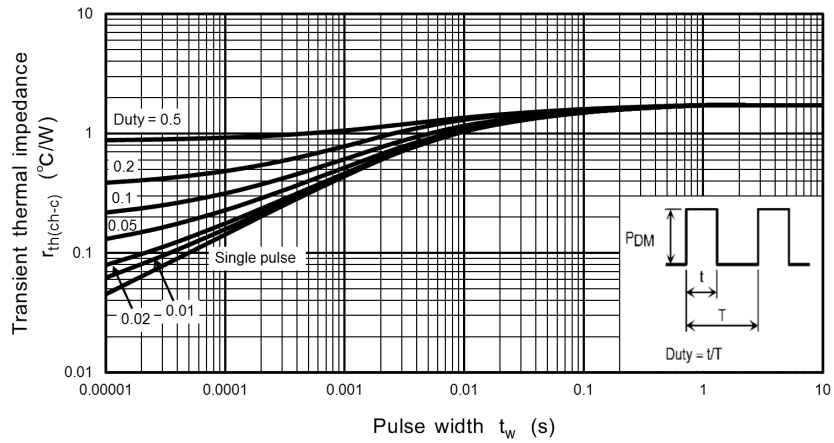
**Fig. 8.10 Dynamic Input/Output Characteristics**



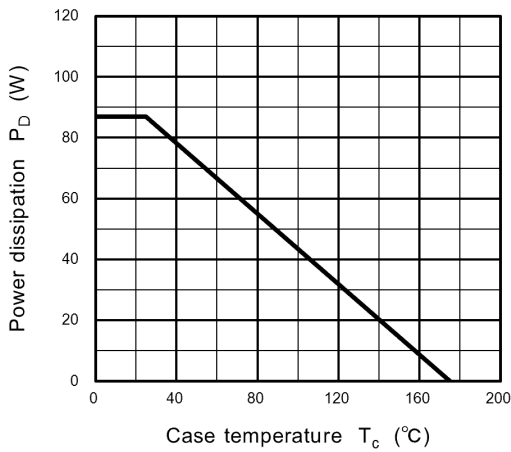
**Fig. 8.11 Capacitance -  $V_{DS}$**



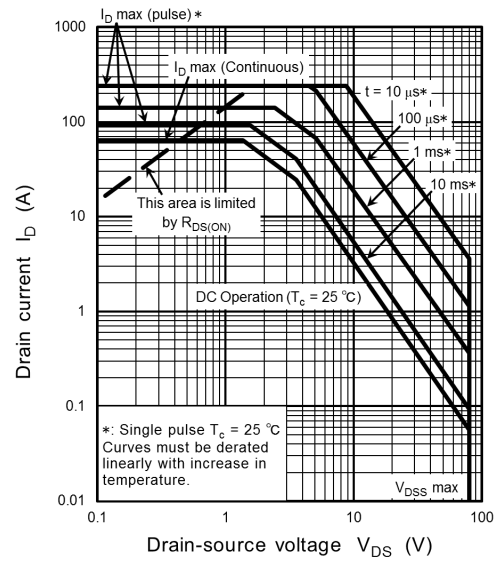
**Fig. 8.12  $Q_{oss} - V_{DS}$**



**Fig. 8.13  $r_{th} - t_w$**   
(Guaranteed Maximum)



**Fig. 8.14  $P_D - T_c$**   
(Guaranteed Maximum)

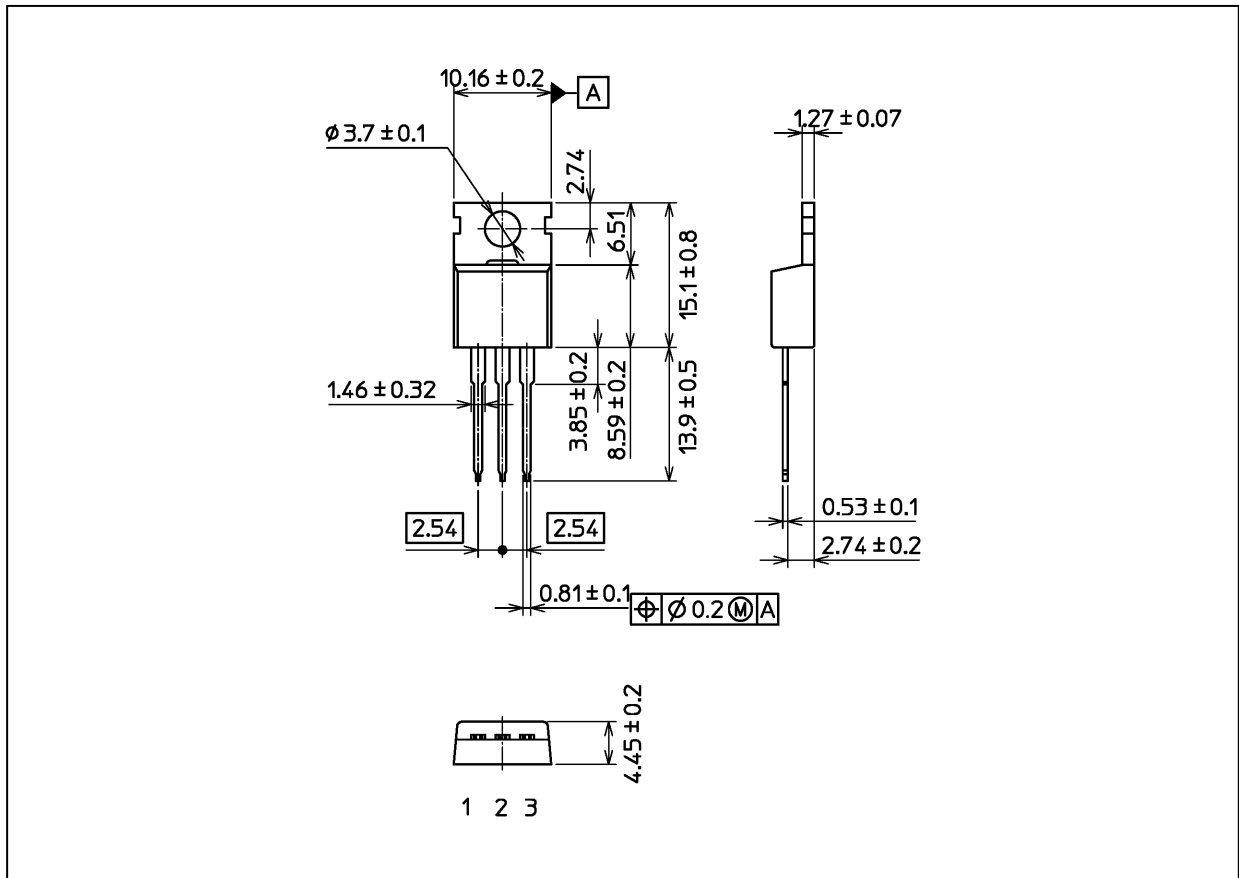


**Fig. 8.15 Safe Operating Area**  
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 1.96 g (typ.)

| Package Name(s)  |
|------------------|
| TOSHIBA: 2-10X1A |
| Nickname: TO-220 |



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